

RGW60TS65

650V 30A Field Stop Trench IGBT

V _{CES}	650V
I _{C (100°C)}	30A
V _{CE(sat) (Typ.)}	1.5V
P_D	178W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

Applications

PFC

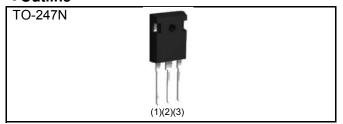
UPS

Welding

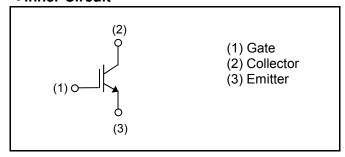
Solar Inverter

ΙH

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube	
	Reel Size (mm)	-	
Typo	Tape Width (mm)	-	
Туре	Basic Ordering Unit (pcs)	450	
	Packing Code	C11	
	Marking	RGW60TS65	

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit	
Collector - Emitter Voltage		V _{CES}	650	V	
Gate - Emitter Voltage		V _{GES}	±30	V	
Collector Current	T _C = 25°C	I _C	60	А	
	T _C = 100°C	I _C 30		А	
Pulsed Collector Current		I _{CP} *1	120	А	
Davier Dissipation	T _C = 25°C	P _D	178	W	
Power Dissipation	T _C = 100°C	P _D	89	W	
Operating Junction Temperature		Tj	-40 to +175	°C	
Storage Temperature		T _{stg}	-55 to +175	°C	

^{*1} Pulse width limited by T_{imax}.

●Thermal Resistance

Parameter	Symbol	Values			Unit
- Faranietei		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.84	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
- arameter	1 drameter Symbol Conditions		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	1	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 20.0 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 30A$, $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	1 1	1.5 1.85	1.9	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Daramatar	Cymphal	Conditions	Values			Linit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	2530	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	65	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	46	-	
Total Gate Charge	Q_g	V _{CE} = 400V	-	84	-	
Gate - Emitter Charge	Q_{ge}	I _C = 30A	-	17	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	31	-	
Turn - on Delay Time	t _{d(on)}	I _C = 30A, V _{CC} = 400V	-	37	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	13	-	
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	114	-	ns
Fall Time	t _f	Inductive Load	-	35	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	0.48	-	
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.49	-	mJ
Turn - on Delay Time	t _{d(on)}	I _C = 30A, V _{CC} = 400V	-	36	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	14	-	no
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	133	-	ns
Fall Time	t _f	Inductive Load	-	76	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	0.49	-	
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.63	-	mJ
		I _C = 120A, V _{CC} = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
1		$R_G = 100\Omega, T_j = 175^{\circ}C$				

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Fig.1 Power Dissipation vs. Case Temperature

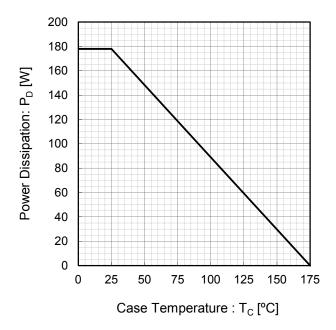


Fig.2 Collector Current vs. Case Temperature

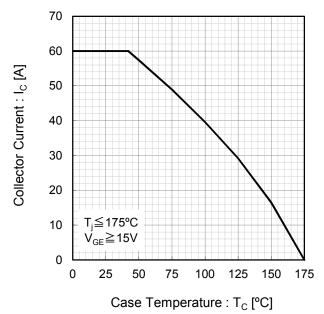


Fig.3 Forward Bias Safe Operating Area

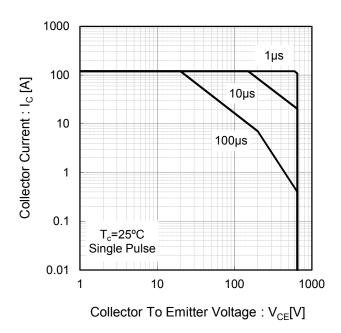


Fig.4 Reverse Bias Safe Operating Area

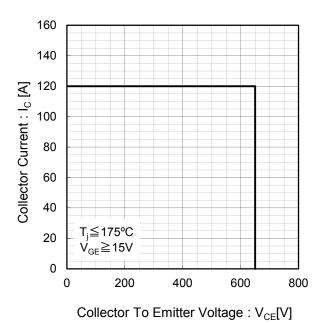


Fig.5 Typical Output Characteristics

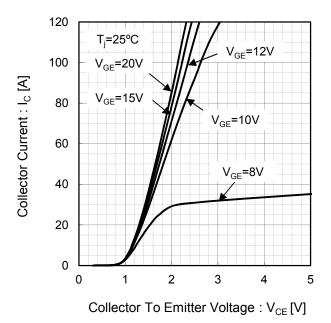
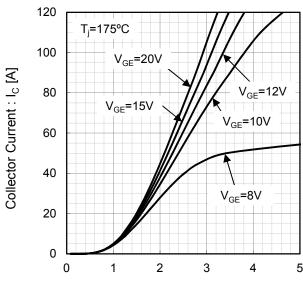


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : $V_{CE}[V]$

Fig.7 Typical Transfer Characteristics

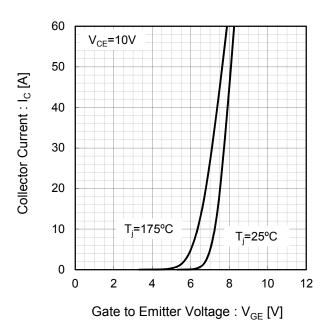


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

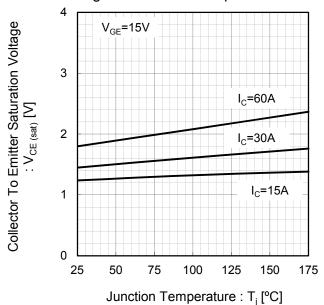


Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

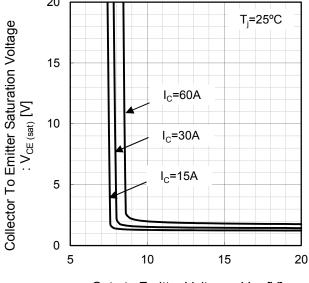
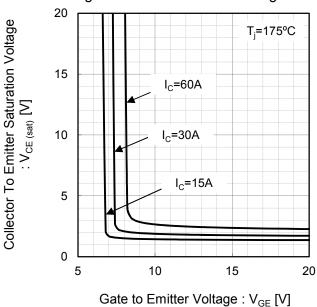


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate to Emitter Voltage : $V_{GE}[V]$

Fig.11 Typical Switching Time vs.

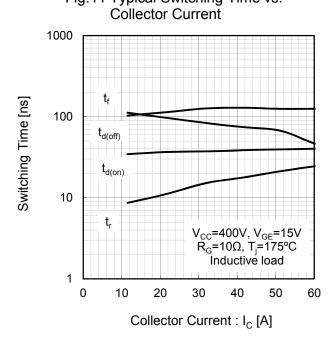


Fig.12 Typical Switching Time vs. Gate Resistance

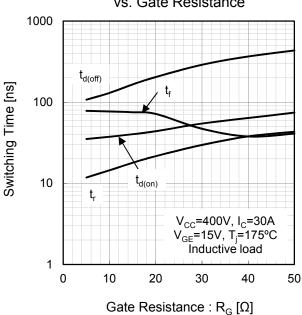


Fig.13 Typical Switching Energy Losses vs. Collector Current

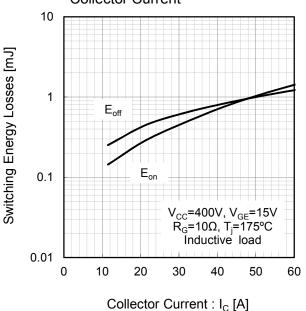


Fig.14 Typical Switching Energy Losses vs. Gate Resistance

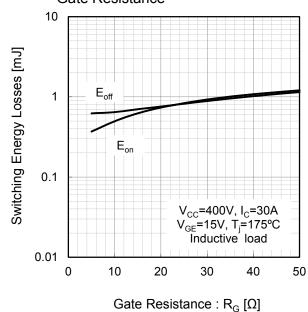
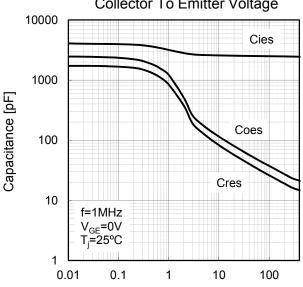
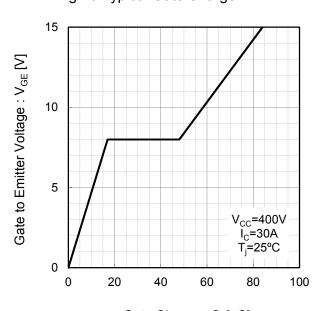


Fig.15 Typical Capacitance vs.
Collector To Emitter Voltage



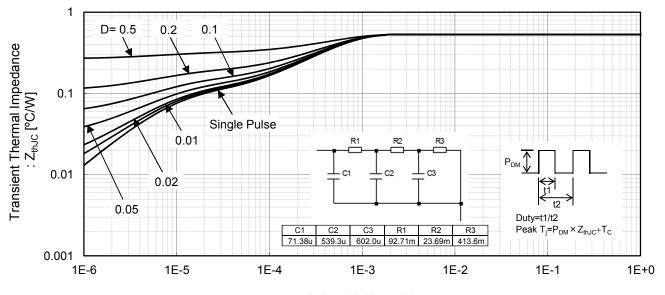
Collector To Emitter Voltage : $V_{CE}[V]$

Fig.16 Typical Gate Charge



Gate Charge : Q_q[nC]

Fig.17 Typical IGBT Transient Thermal Impedance



Pulse Width: t1[s]

•Inductive Load Switching Circuit and Waveform

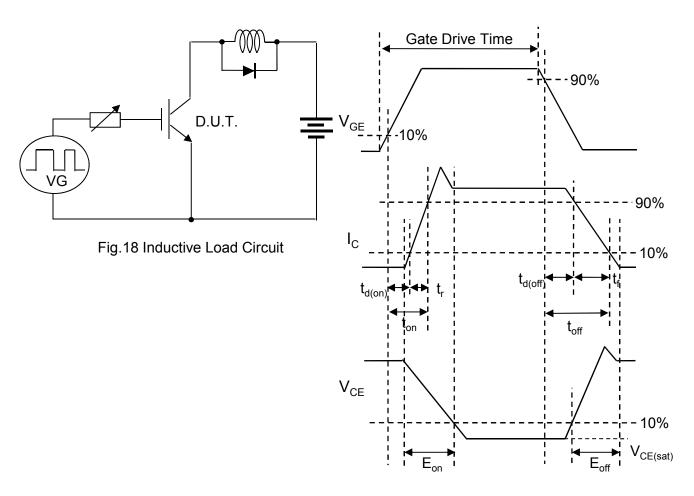


Fig.19 Inductive Load Waveform

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